# TOSHIBA

## MICROWAVE POWER GAN HEMT **TGI5867-50L**

MICROWAVE SEMICONDUCTOR TECHNICAL DATA

#### **FEATURES**

**·BROAD BAND INTERNALLY MATCHED HEMT** 

#### ·HIGH POWER

Pout= 47.0dBm at Pin= 39.0dBm

#### ·HIGH GAIN

GL= 13.5dB at 5.85GHz to 6.75GHz

#### ·LOW INTERMODULATION DISTORTION

IM3(Min.)= -40dBc at Po=32.0dBm Single Carrier Level

#### ·HERMETICALLY SEALED PACKAGE



<b>RF PERFORMANCE SPECIFICATIONS</b>	( Ta= 25°C )	

CHARACTERISTICS	SYMBOL	CONDITIONS	UNIT	MIN.	TYP.	MAX.
Output Power	Pout	VDS= 24V	dBm	46.0	47.0	
Drain Current	IDS1	IDSset= 3.0A f= 5.85 to 6.75GHz @Pin= 39.0dBm	А		5.4	6.3
Power Added Efficiency	ηadd		%	_	33	
Linear Gain	GL	@Pin= 20dBm	dB	12.5	13.5	_
Gain flatness	ΔG	*	dB	_	_	±0.8
3rd Order Intermodulation Distortion	IM3	Two-Tone Test	dBc	-40	_	
Drain Current	IDS2	Po= 32.0dBm, ∆f= 5MHz (Single Carrier Level)	А		3.5	4.5
Channel Temperature Rise	∆Tch	(VDS X IDS + Pin – P1dB) X Rth(c-c)	°C		130	150

Recommended Gate Resistance(Rg): 60 Ω

## ELECTRICAL CHARACTERISTICS (Ta= 25°C)

CHARACTERISTICS	SYMBOL	CONDITIONS	UNIT	MIN.	TYP.	MAX.
Transconductance	gm	VDS= 5V IDS= 5.0A	S	_	4.5	_
Pinch-off Voltage	VGSoff	VDS= 5V IDS= 23mA	V	-2.6	-4.0	-6.0
Saturated Drain Current	IDSS	VDS= 5V VGS= 0V	А		15.0	18.0
Gate-Source Breakdown Voltage	VGSO	IGS= -10mA	V	-10.0	_	_
Thermal Resistance	Rth(c-c)	Channel to Case	°C/W		1.4	1.6

◆ The information contained herein is presented as guidance for product use. No responsibility is assumed by TOSHIBA for any infringement of patents or any other intellectual property rights of third parties that may result from the use of product. No license to any intellectual property right is granted by this document. The information contained herein is subject to change without prior notice. It is advisable to contact TOSHIBA before proceeding with design of equipment incorporating this product.

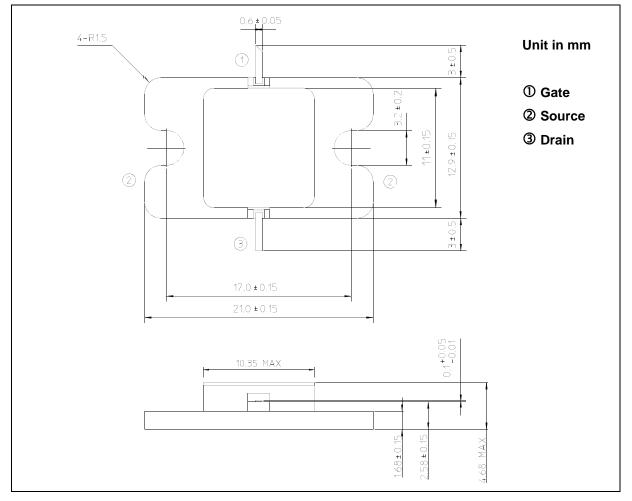
## TOSHIBA

MICROWAVE SEMICONDUCTOR TECHNICAL DATA

## ABSOLUTE MAXIMUM RATINGS (Ta= 25°C)

CHARACTERISTICS	SYMBOL	UNIT	RATING
Drain-Source Voltage	VDS	V	50
Gate-Source Voltage	VGS	V	-10
Drain Current	IDS	A	15
Total Power Dissipation (Tc= 25 °C)	PT	W	140
Channel Temperature	Tch	°C	250
Storage Temperature	Tstg	°C	-65 to +175

### PACKAGE OUTLINE (7-AA04A)



### HANDLING PRECAUTIONS FOR PACKAGE MODEL

Soldering iron should be grounded and the operating time should not exceed 10 seconds at 260°C or 3 seconds at 350°C.